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What is "Embedded - Microcontrollers"?

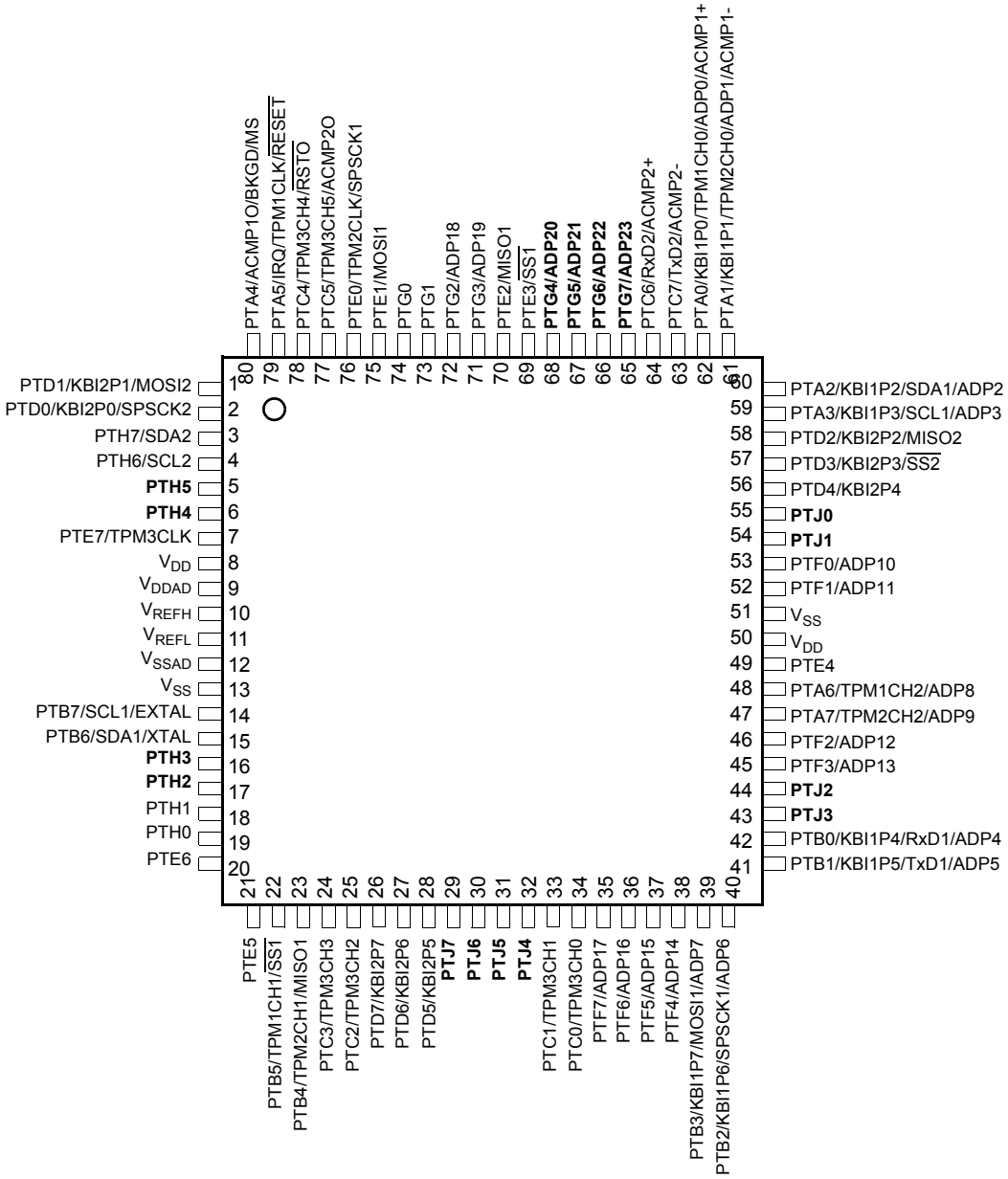
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	50MHz
Connectivity	I²C, LINbus, SCI, SPI
Peripherals	LVD, PWM, WDT
Number of I/O	54
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 22x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s08qe64clh

2 Pin Assignments

This section describes the pin assignments for the available packages. See Table 2 for pin availability by package pin-count.



Pins in **bold** are added from the next smaller package.

Figure 2. Pin Assignments in 80-Pin LQFP

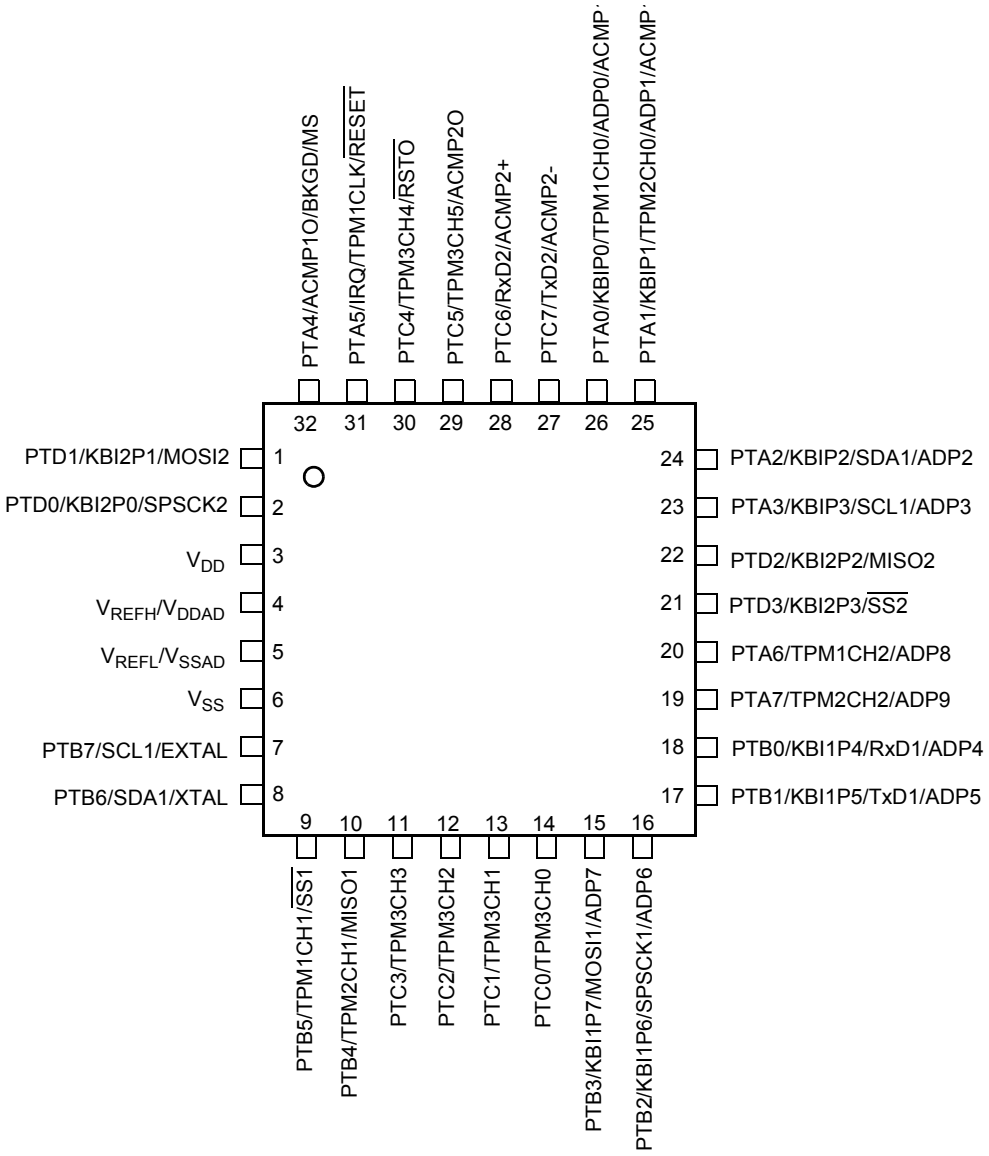


Figure 6. Pin Assignments 32-Pin LQFP Package

Table 2. MC9S08QE128 Series Pin Assignment by Package and Pin Count

Pin Number					Lowest ←		Priority →		Highest
80	**64**	**48**	**44**	**32**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt 3**	**Alt 4**
1	1	1	1	1	PTD1	KBI2P1	MOSI2		
2	2	2	2	2	PTD0	KBI2P0	SPSCK2		
3	3	—	—	—	PTH7	SDA2			
4	4	—	—	—	PTH6	SCL2			
5	—	—	—	—	PTH5				
6	—	—	—	—	PTH4				
7	5	3	3	—	PTE7	TPM3CLK			
8	6	4	4	3					V_{DD}
9	7	5	5	4					V_{DDA}
10	8	6	6	—					V_{REFH}
11	9	7	7	—					V_{REFL}
12	10	8	8	5					V_{SSA}
13	11	9	9	6					V_{SS}
14	12	10	10	7	PTB7	SCL1			EXTAL
15	13	11	11	8	PTB6	SDA1			XTAL
16	—	—	—	—	PTH3				
17	—	—	—	—	PTH2				
18	14	—	—	—	PTH1				
19	15	—	—	—	PTH0				
20	16	12	—	—	PTE6				
21	17	13	—	—	PTE5				
22	18	14	12	9	PTB5	TPM1CH1	$\overline{SS1}$		
23	19	15	13	10	PTB4	TPM2CH1	MISO1		
24	20	16	14	11	PTC3	TPM3CH3			
25	21	17	15	12	PTC2	TPM3CH2			
26	22	18	16	—	PTD7	KBI2P7			
27	23	19	17	—	PTD6	KBI2P6			
28	24	20	18	—	PTD5	KBI2P5			
29	—	—	—	—	PTJ7				
30	—	—	—	—	PTJ6				
31	—	—	—	—	PTJ5				
32	—	—	—	—	PTJ4				
33	25	21	19	13	PTC1	TPM3CH1			
34	26	22	20	14	PTC0	TPM3CH0			
35	27	—	—	—	PTF7				ADP17
36	28	—	—	—	PTF6				ADP16
37	29	—	—	—	PTF5				ADP15
38	30	—	—	—	PTF4				ADP14
39	31	23	21	15	PTB3	KBI1P7	MOSI1		ADP7
40	32	24	22	16	PTB2	KBI1P6	SPSCK1		ADP6

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_D = K \div (T_J + 273°C) \quad \textit{Eqn. 2}$$

Solving Equation 1 and Equation 2 for K gives:

$$K = P_D \times (T_A + 273°C) + \theta_{JA} \times (P_D)^2 \quad \textit{Eqn. 3}$$

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

3.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions should be used to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits. During the device qualification ESD stresses were performed for the human body model (HBM), the machine model (MM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 6. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	3	
Machine	Series resistance	R1	0	Ω
	Storage capacitance	C	200	pF
	Number of pulses per pin	—	3	
Latch-up	Minimum input voltage limit		– 2.5	V
	Maximum input voltage limit		7.5	V

Table 7. ESD and Latch-Up Protection Characteristics

No.	Rating[1]	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	± 2000	—	V
2	Machine model (MM)	V_{MM}	± 200	—	V
3	Charge device model (CDM)	V_{CDM}	± 500	—	V
4	Latch-up current at T_A = 85°C	I_{LAT}	± 100	—	mA

1 Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

Table 12. ICS Frequency Specifications (Temperature Range = –40 to 85°C Ambient) (continued)

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
8	C	Total deviation of trimmed DCO output frequency over voltage and temperature	Δf_{dco_t}	—	+ 0.5 -1.0	± 2	$\%f_{dco}$
9	C	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of 0°C to 70 °C	Δf_{dco_t}	—	± 0.5	± 1	$\%f_{dco}$
10	C	FLL acquisition time [3]	$t_{Acquire}$	—	—	1	ms
11	C	Long term jitter of DCO output clock (averaged over 2-ms interval) [4]	C_{Jitter}	—	0.02	0.2	$\%f_{dco}$

1 Data in Typical column was characterized at 3.0 V, 25°C or is typical recommended value.

2 The resulting bus clock frequency should not exceed the maximum specified bus clock frequency of the device.

3 This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (FBELP, FBILP) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

4 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{Bus}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry via V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

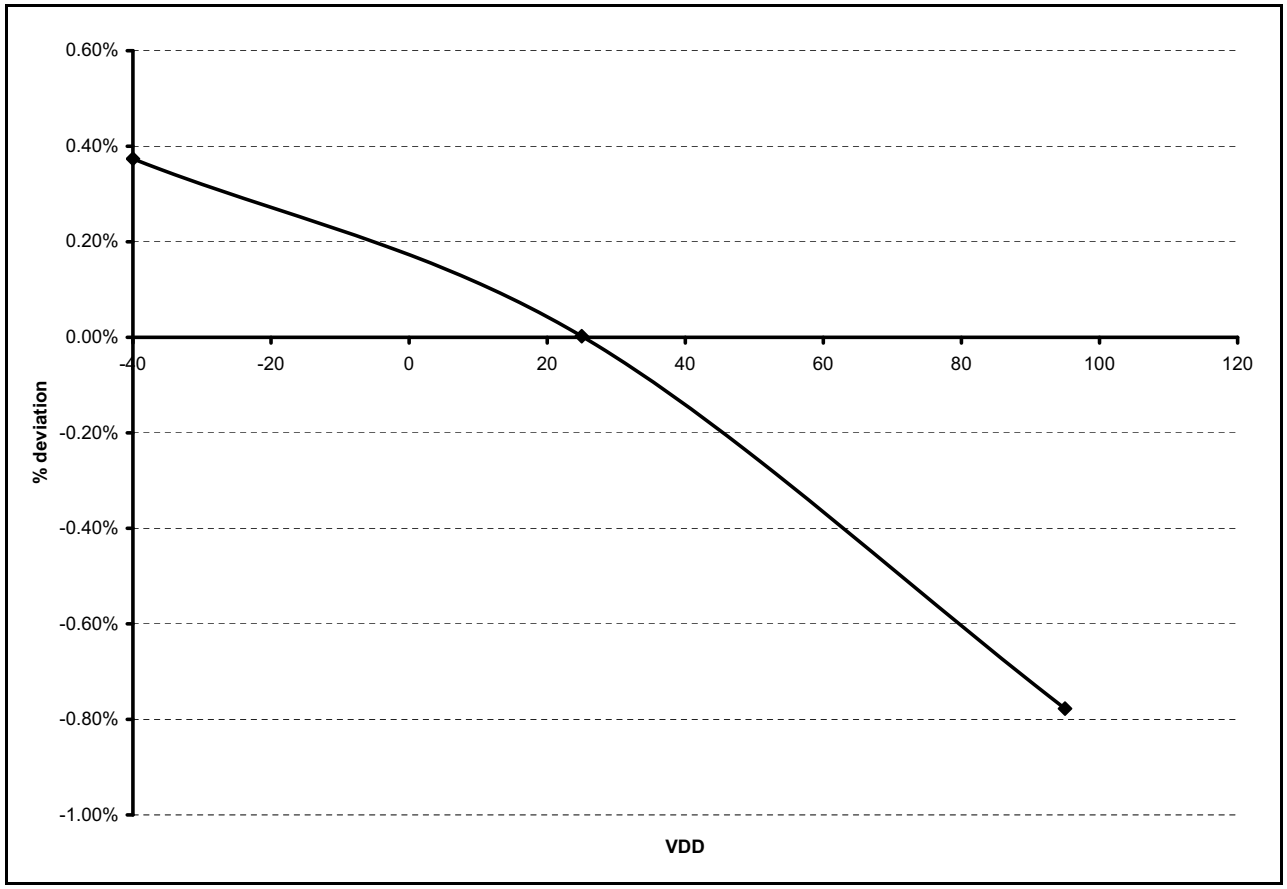


Figure 15. Deviation of DCO Output Across Temperature at V_{DD} = 3.0 V

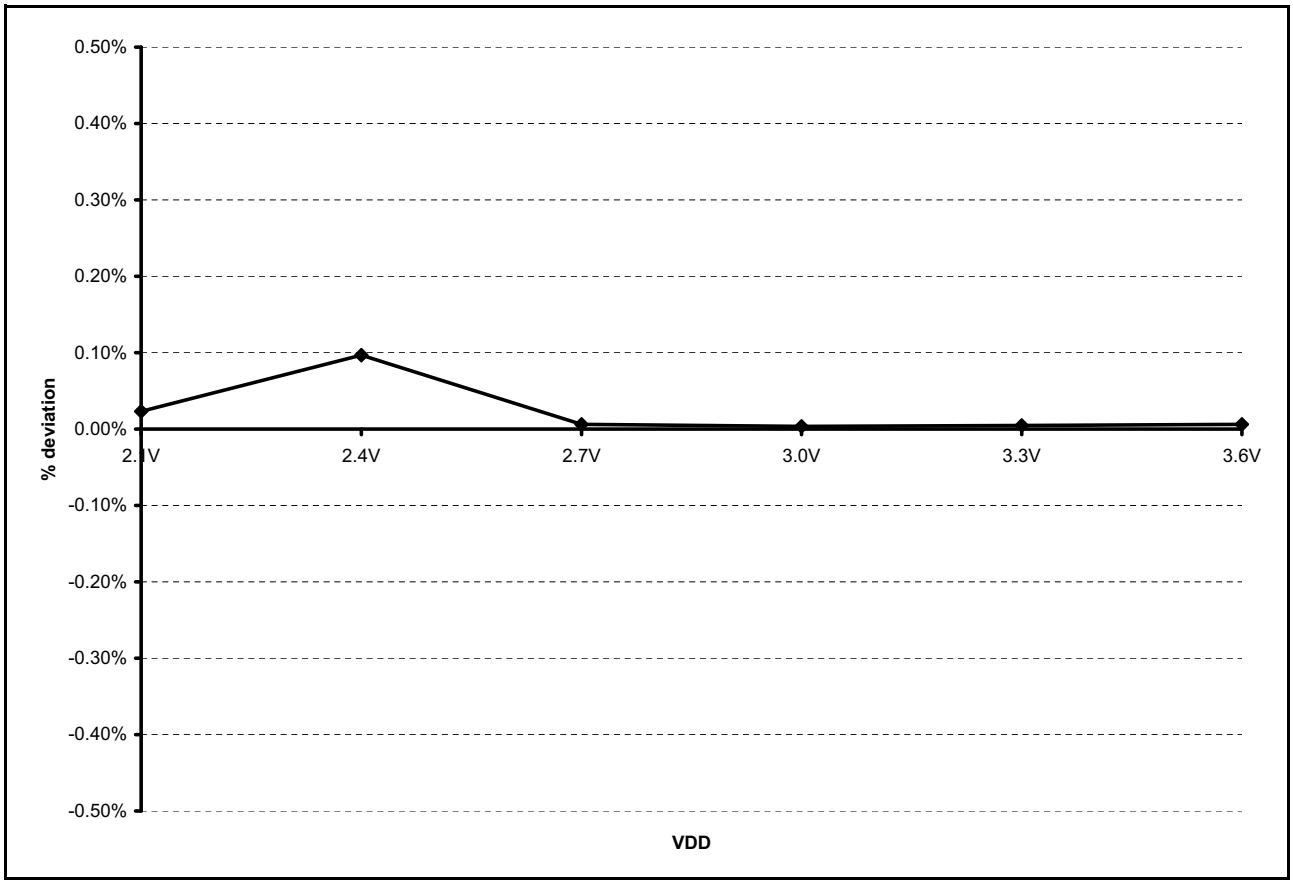


Figure 16. Deviation of DCO Output Across V_{DD} at 25°C

3.10 AC Characteristics

This section describes timing characteristics for each peripheral system.

3.10.1 Control Timing

Table 13. Control Timing

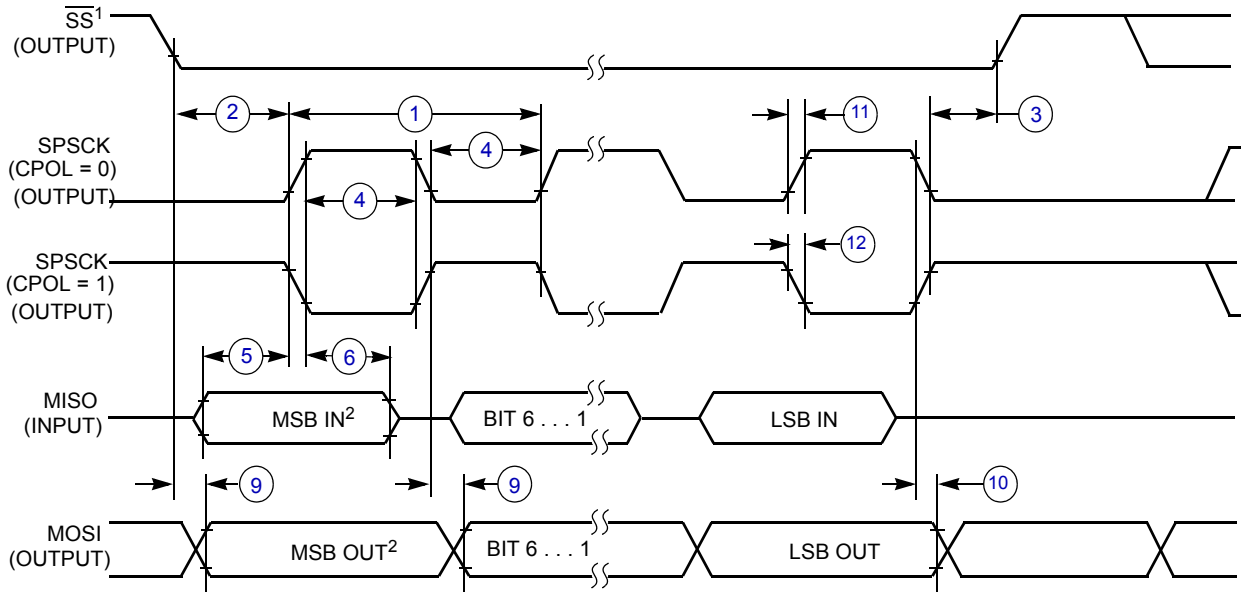
Num	C	Rating	Symbol	Min	Typ[1]	Max	Unit
1	D	Bus frequency (t_{cyc} = 1/f_{Bus}) $V_{DD} \geq 1.8V$ $V_{DD} > 2.1V$ $V_{DD} > 2.4V$	f_{Bus}	dc	— — —	10 20 25.165	MHz
2	D	Internal low power oscillator period	t_{LPO}	700	—	1300	µs
3	D	External reset pulse width[2]	t_{extrst}	100	—	—	ns
4	D	Reset low drive	t_{rstdrv}	34 x t_{cyc}	—	—	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t_{MSSU}	500	—	—	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes [3]	t_{MSH}	100	—	—	µs

3.10.3 SPI Timing

Table 15 and Figure 21 through Figure 24 describe the timing requirements for the SPI system.

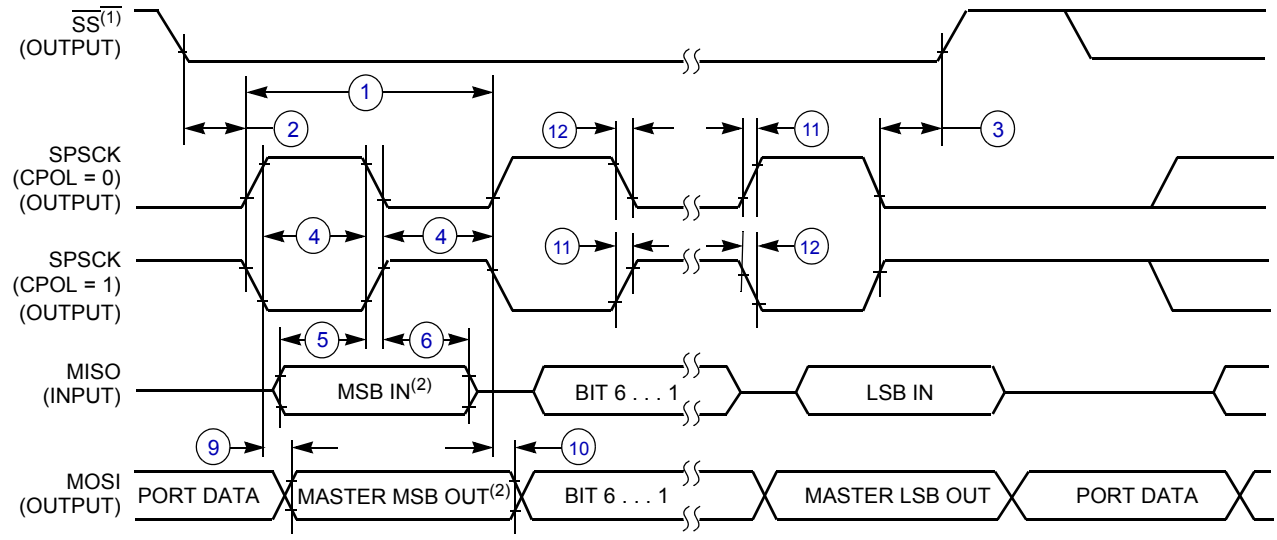
Table 15. SPI Timing

No.	C	Function	Symbol	Min	Max	Unit
—	D	Operating frequency Master Slave	f_{op}	 $f_{Bus}/2048$ 0	 $f_{Bus}/2$ $f_{Bus}/4$	 Hz Hz
1	D	SPSCK period Master Slave	t_{SPSCK}	 2 4	 2048 —	 t_{cyc} t_{cyc}
2	D	Enable lead time Master Slave	t_{Lead}	 1/2 1	 — —	 t_{SPSCK} t_{cyc}
3	D	Enable lag time Master Slave	t_{Lag}	 1/2 1	 — —	 t_{SPSCK} t_{cyc}
4	D	Clock (SPSCK) high or low time Master Slave	t_{WSPSCK}	 $t_{cyc} - 30$ $t_{cyc} - 30$	 1024 t_{cyc} —	 ns ns
5	D	Data setup time (inputs) Master Slave	t_{SU}	 15 15	 — —	 ns ns
6	D	Data hold time (inputs) Master Slave	t_{HI}	 0 25	 — —	 ns ns
7	D	Slave access time	t_a	—	1	t_{cyc}
8	D	Slave MISO disable time	t_{dis}	—	1	t_{cyc}
9	D	Data valid (after SPSCK edge) Master Slave	t_v	 — —	 25 25	 ns ns
10	D	Data hold time (outputs) Master Slave	t_{HO}	 0 0	 — —	 ns ns
11	D	Rise time Input Output	 t_{RI} t_{RO}	 — —	 $t_{cyc} - 25$ 25	 ns ns
12	D	Fall time Input Output	 t_{FI} t_{FO}	 — —	 $t_{cyc} - 25$ 25	 ns ns



NOTES:
1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 21. SPI Master Timing (CPHA = 0)



NOTES:
1. $\overline{SS}$ output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 22. SPI Master Timing (CPHA =1)

3.11 Analog Comparator (ACMP) Electricals

Table 16. Analog Comparator Electrical Specifications

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DD}	1.80	—	3.6	V
C	Supply current (active)	I_{DDAC}	—	20	35	µA
D	Analog input voltage	V_{AIN}	V_{SS} – 0.3	—	V_{DD}	V
C	Analog input offset voltage	V_{AIO}		20	40	mV
C	Analog comparator hysteresis	V_H	3.0	9.0	15.0	mV
P	Analog input leakage current	I_{ALKG}	—	—	1.0	µA
C	Analog comparator initialization delay	t_{AINIT}	—	—	1.0	µs

3.12 ADC Characteristics

Table 17. 12-bit ADC Operating Conditions

C	Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
D	Supply voltage	Absolute	V_{DDAD}	1.8	—	3.6	V	
		Delta to V_{DD} (V_{DD}-V_{DDAD})[2]	ΔV_{DDAD}	-100	0	+100	mV	
D	Ground voltage	Delta to V_{SS} (V_{SS}-V_{SSAD})[2]	ΔV_{SSAD}	-100	0	+100	mV	
D	Ref Voltage High		V_{REFH}	1.8	V_{DDAD}	V_{DDAD}	V	
D	Ref Voltage Low		V_{REFL}	V_{SSAD}	V_{SSAD}	V_{SSAD}	V	
D	Input Voltage		V_{ADIN}	V_{REFL}	—	V_{REFH}	V	
C	Input Capacitance		C_{ADIN}	—	4.5	5.5	pF	
C	Input Resistance		R_{ADIN}	—	5	7	kΩ	
C	Analog Source Resistance	12 bit mode f_{ADCK} > 4MHz f_{ADCK} < 4MHz	R_{AS}	 — —	 — —	 2 5	kΩ	External to MCU
		10 bit mode f_{ADCK} > 4MHz f_{ADCK} < 4MHz		 — —	 — —	 5 10		
		8 bit mode (all valid f_{ADCK})		—	—	10		
D	ADC Conversion Clock Freq.	High Speed (ADLPC=0)	f_{ADCK}	0.4	—	8.0	MHz	
		Low Power (ADLPC=1)		0.4	—	4.0		

1 Typical values assume V_{DDAD} = 3.0V, Temp = 25°C, f_{ADCK}=1.0MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 DC potential difference.

Table 18. 12-bit ADC Characteristics (V_{REFH} = V_{DDAD}, V_{REFL} = V_{SSAD}) (continued)

Characteristic	Conditions	C	Symb	Min	Typ[1]	Max	Unit	Comment
Conversion Time (Including sample time)	Short Sample (ADLSMP=0)	P	t_{ADC}	—	20	—	ADCK cycles	See the ADC chapter in the MC9S08*QE128 Reference Manual* for conversion time variances
	Long Sample (ADLSMP=1)	C		—	40	—		
Sample Time	Short Sample (ADLSMP=0)	P	t_{ADS}	—	3.5	—	ADCK cycles	
	Long Sample (ADLSMP=1)	C		—	23.5	—		
Total Unadjusted Error	12 bit mode	T	E_{TUE}	—	±3.0	—	LSB[2]	Includes Quantization
	10 bit mode	P		—	±1	±2.5		
	8 bit mode	T		—	±0.5	±1.0		
Differential Non-Linearity	12 bit mode	T	DNL	—	±1.75	—	LSB[2]	
	10 bit mode[3]	P		—	±0.5	±1.0		
	8 bit mode[3]	T		—	±0.3	±0.5		
Integral Non-Linearity	12 bit mode	T	INL	—	±1.5	—	LSB[2]	
	10 bit mode	T		—	±0.5	±1.0		
	8 bit mode	T		—	±0.3	±0.5		
Zero-Scale Error	12 bit mode	T	E_{ZS}	—	±1.5	—	LSB[2]	V_{ADIN} = V_{SSAD}
	10 bit mode	P		—	±0.5	±1.5		
	8 bit mode	T		—	±0.5	±0.5		
Full-Scale Error	12 bit mode	T	E_{FS}	—	±1.0	—	LSB[2]	V_{ADIN} = V_{DDAD}
	10 bit mode	P		—	±0.5	±1		
	8 bit mode	T		—	±0.5	±0.5		
Quantization Error	12 bit mode	D	E_Q	—	-1 to 0	—	LSB[2]	
	10 bit mode			—	—	±0.5		
	8 bit mode			—	—	±0.5		
Input Leakage Error	12 bit mode	D	E_{IL}	—	±2	—	LSB[2]	Pad leakage[4] * R_{AS}
	10 bit mode			—	±0.2	±4		
	8 bit mode			—	±0.1	±1.2		
Temp Sensor Slope	-40°C to 25°C	D	m	—	1.646	—	mV/°C	
	25°C to 85°C			—	1.769	—		
Temp Sensor Voltage	25°C	D	V_{TEMP25}	—	701.2	—	mV	

1 Typical values assume V_{DDAD} = 3.0V, Temp = 25°C, f_{ADCK}=1.0MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 1 LSB = $(V_{REFH} - V_{REFL})/2^N$

3 Monotonicity and No-Missing-Codes guaranteed in 10 bit and 8 bit modes

4 Based on input pad leakage current. Refer to pad electricals.

3.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory section of the *MC9S08QE128 Reference Manual*.

Table 19. Flash Characteristics

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage for program/erase -40°C to 85°C	$V_{prog/erase}$	1.8		3.6	V
D	Supply voltage for read operation	V_{Read}	1.8		3.6	V
D	Internal FCLK frequency[1]	f_{FCLK}	150		200	kHz
D	Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	µs
P	Byte program time (random location)(2)	t_{prog}		9		t_{Fcyc}
P	Byte program time (burst mode)(2)	t_{Burst}		4		t_{Fcyc}
P	Page erase time[2]	t_{Page}		4000		t_{Fcyc}
P	Mass erase time(2)	t_{Mass}		20,000		t_{Fcyc}
	Byte program current[3]	R_{IDDBP}	—	4	—	mA
	Page erase current[3]	R_{IDDPE}	—	6	—	mA
C	Program/erase endurance[4] T_L to T_H = –40°C to + 85°C T = 25°C		10,000 —	— 100,000	— —	cycles
C	Data retention[5]	t_{D_ret}	15	100	—	years

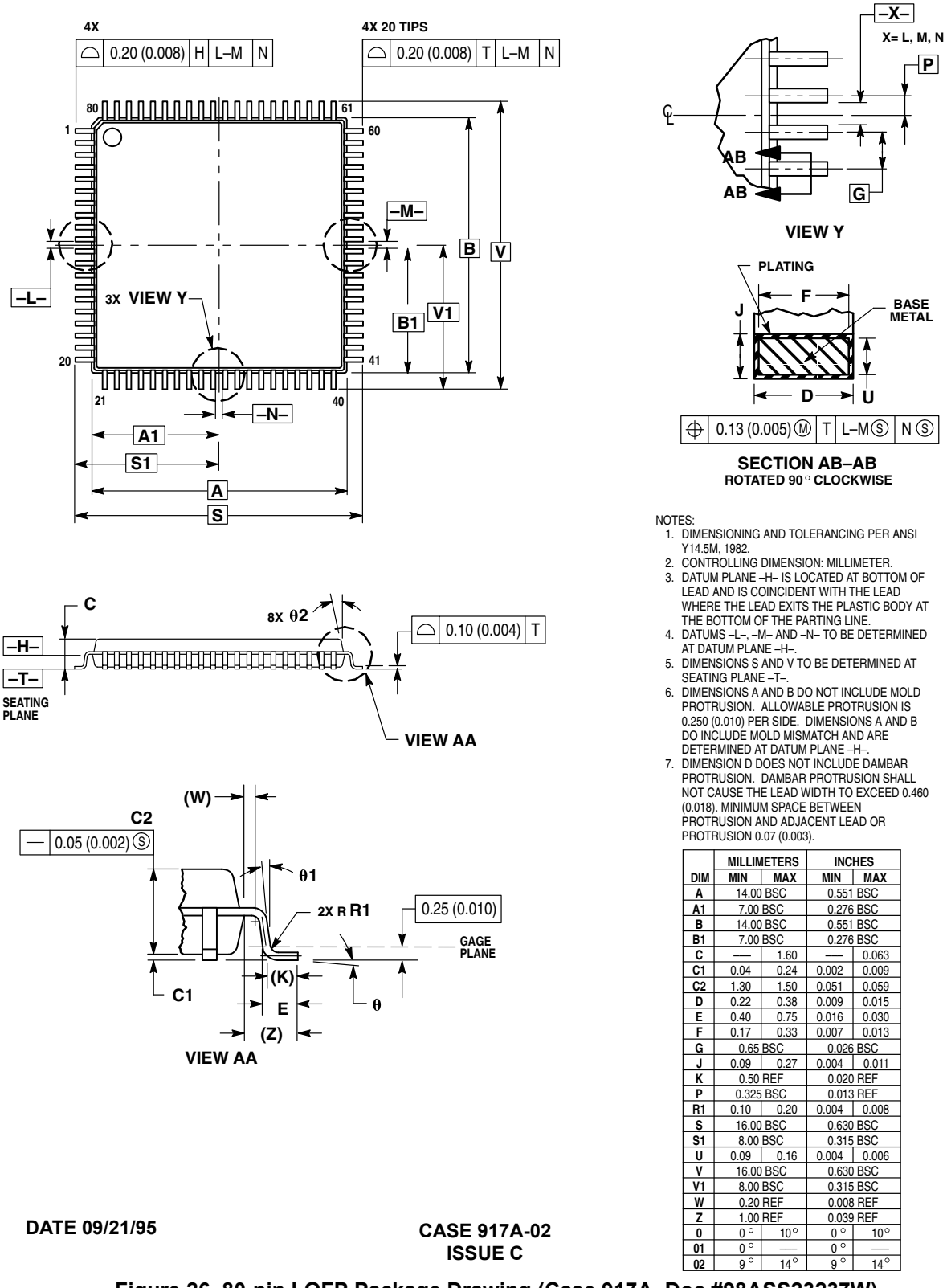
1 The frequency of this clock is controlled by a software setting.

2 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

3 The program and erase currents are additional to the standard run I_{DD}. These values are measured at room temperatures with V_{DD} = 3.0 V, bus frequency = 4.0 MHz.

4 **Typical endurance for flash** was evaluated for this product family on the HC9S12Dx64. For additional information on how Freescale defines typical endurance, please refer to Engineering Bulletin EB619, *Typical Endurance for Nonvolatile Memory*.

5 **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale defines typical data retention, please refer to Engineering Bulletin EB618, *Typical Data Retention for Nonvolatile Memory.*



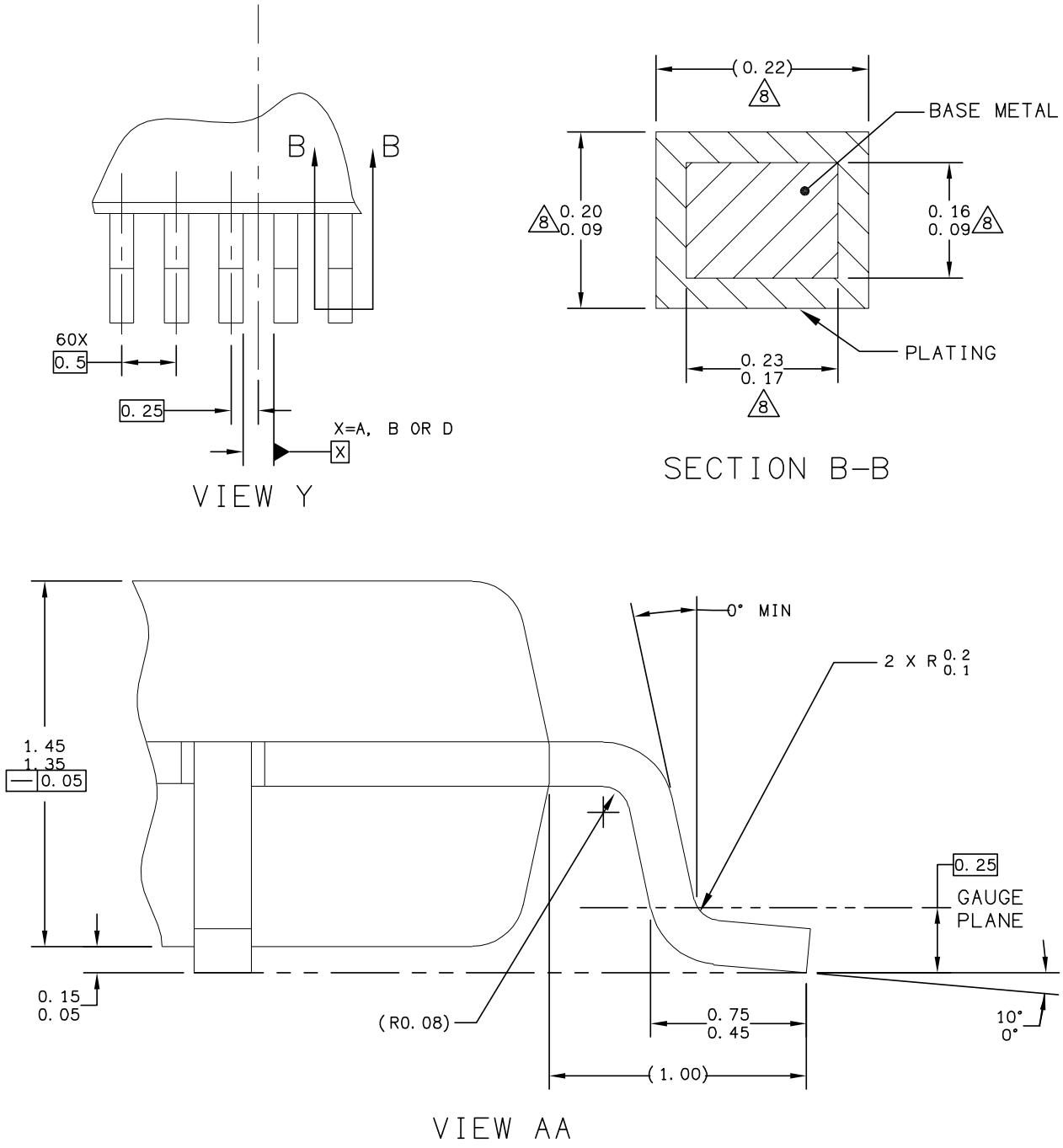
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DATUM PLANE –H– IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
4. DATUMS –L–, –M– AND –N– TO BE DETERMINED AT DATUM PLANE –H–.
5. DIMENSIONS S AND V TO BE DETERMINED AT SEATING PLANE –T–.
6. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.250 (0.010) PER SIDE. DIMENSIONS A AND B DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE –H–.
7. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.460 (0.018). MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION 0.07 (0.003).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	14.00 BSC		0.551 BSC	
A1	7.00 BSC		0.276 BSC	
B	14.00 BSC		0.551 BSC	
B1	7.00 BSC		0.276 BSC	
C	—	1.60	—	0.063
C1	0.04	0.24	0.002	0.009
C2	1.30	1.50	0.051	0.059
D	0.22	0.38	0.009	0.015
E	0.40	0.75	0.016	0.030
F	0.17	0.33	0.007	0.013
G	0.65 BSC		0.026 BSC	
J	0.09	0.27	0.004	0.011
K	0.50 REF		0.020 REF	
P	0.325 BSC		0.013 REF	
R1	0.10	0.20	0.004	0.008
S	16.00 BSC		0.630 BSC	
S1	8.00 BSC		0.315 BSC	
U	0.09	0.16	0.004	0.006
V	16.00 BSC		0.630 BSC	
V1	8.00 BSC		0.315 BSC	
W	0.20 REF		0.008 REF	
Z	1.00 REF		0.039 REF	
θ	0°	10°	0°	10°
θ1	0°	—	0°	—
θ2	9°	14°	9°	14°

DATE 09/21/95

CASE 917A-02
ISSUE C

Figure 26. 80-pin LQFP Package Drawing (Case 917A, Doc #98ASS23237W)



© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE
TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	DOCUMENT NO: 98ASS23234W	REV: D
	CASE NUMBER: 840F-02	06 APR 2005
	STANDARD: JEDEC MS-026 BCD	

Figure 28. 64-pin LQFP Package Drawing (Case 840F, Doc #98ASS23234W), Sheet 2 of 3

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.
4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
5. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08 mm AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 mm.
6. THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.
7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.
8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 mm AND 0.25 mm FROM THE LEAD TIP.

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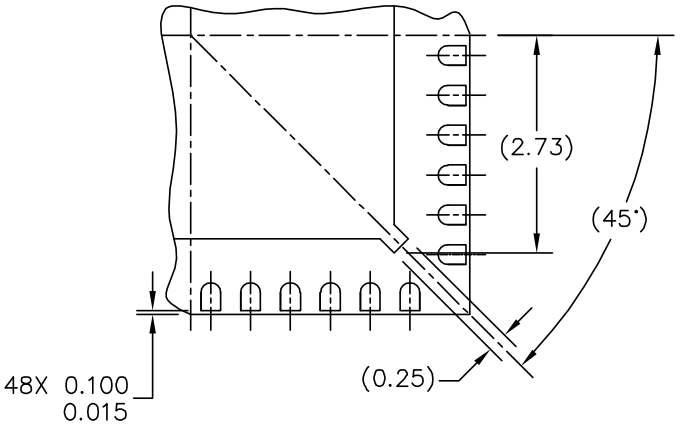
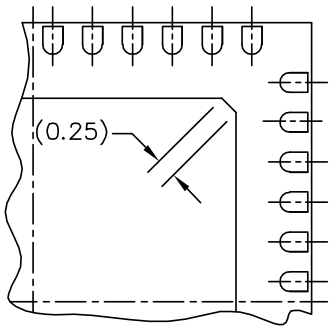
TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	DOCUMENT NO: 98ASS23234W	REV: D	
	CASE NUMBER: 840F-02	06 APR 2005	
	STANDARD: JEDEC MS-026 BCD		

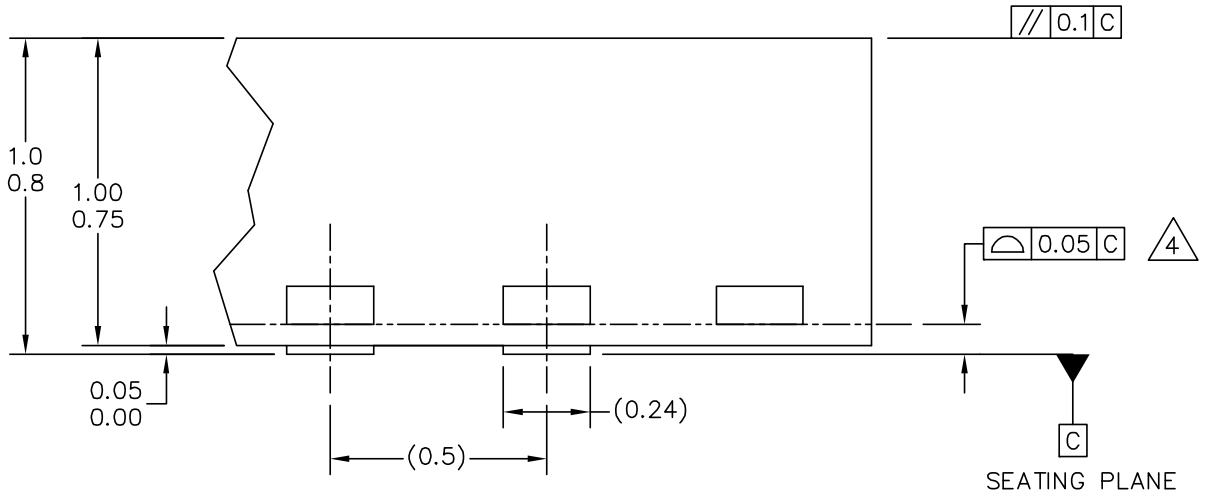
Figure 29. 64-pin LQFP Package Drawing (Case 840F, Doc #98ASS23234W), Sheet 3 of 3



DETAIL N
PREFERRED CORNER CONFIGURATION



DETAIL M
PREFERED PIN 1 BACKSIDE IDENTIFIER



DETAIL G
VIEW ROTATED 90° CW

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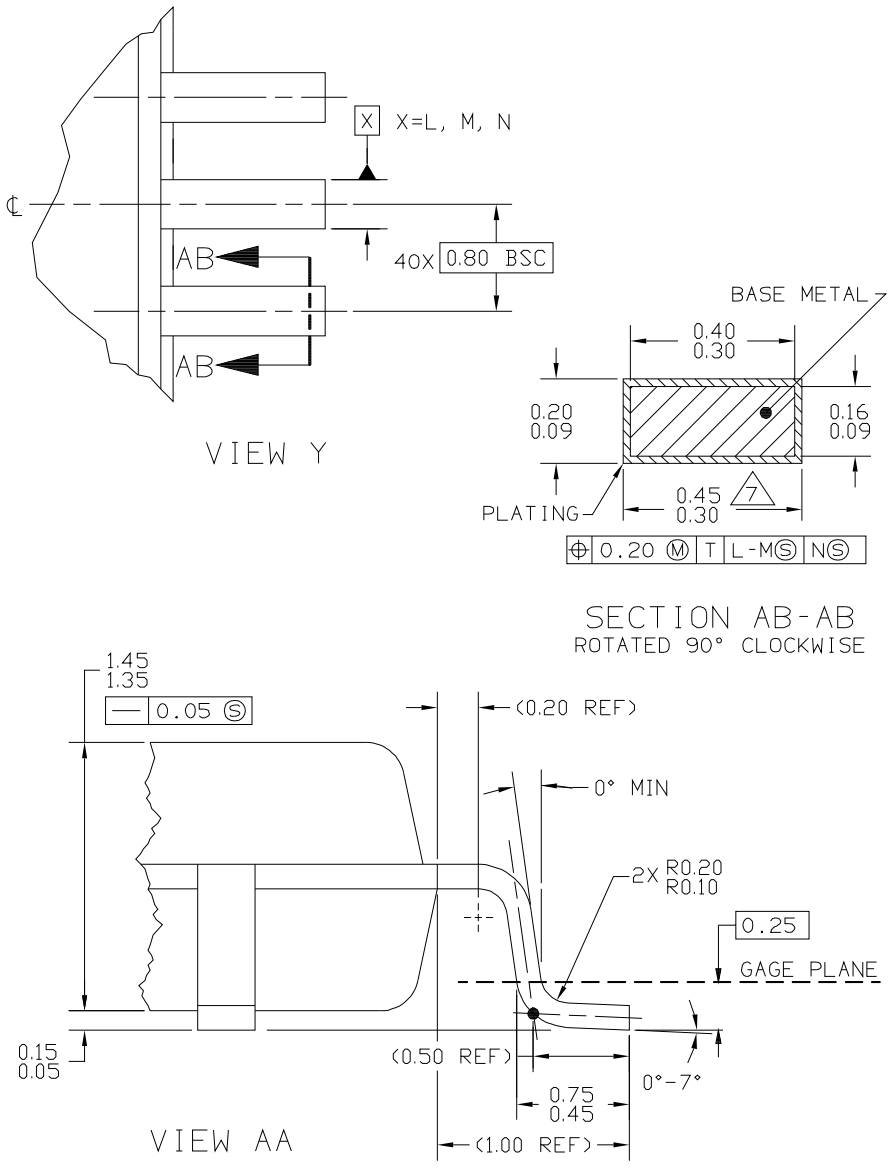
TITLE: THERMALLY ENHANCED QUAD FLAT NON–LEADED PACKAGE (QFN) 48 TERMINAL, 0.5 PITCH (7 X 7 X 1)	DOCUMENT NO: 98ARH99048A	REV: F
	CASE NUMBER: 1314–05	05 DEC 2005
	STANDARD: JEDEC–MO–220 VKKD–2	

Figure 31. 48-pin QFN Package Drawing (Case 1314, Doc #98ARH99048A), Sheet 2 of 3



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TITLE: 44 LD LQFP, 10 X 10 PKG, 0.8 PITCH, 1.4 THICK	DOCUMENT NO: 98ASS23225W	REV: D
	CASE NUMBER: 824D-02	26 FEB 2007
	STANDARD: JEDEC MS-026 BCB	

Figure 34. 44-pin LQFP Package Drawing (Case 824D, Doc #98ASS23225W), Sheet 2 of 3

NOTES:

1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M–1994.

2. CONTROLLING DIMENSION: MILLIMETER

3. DATUM PLANE H IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.

4. DATUMS L, M AND N TO BE DETERMINED AT DATUM PLANE H.

5. DIMENSIONS TO BE DETERMINED AT SEATING PLANE T.

6. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 PER SIDE. DIMENSIONS DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.

7. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE DIMENSION TO EXCEED 0.53. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION 0.07.

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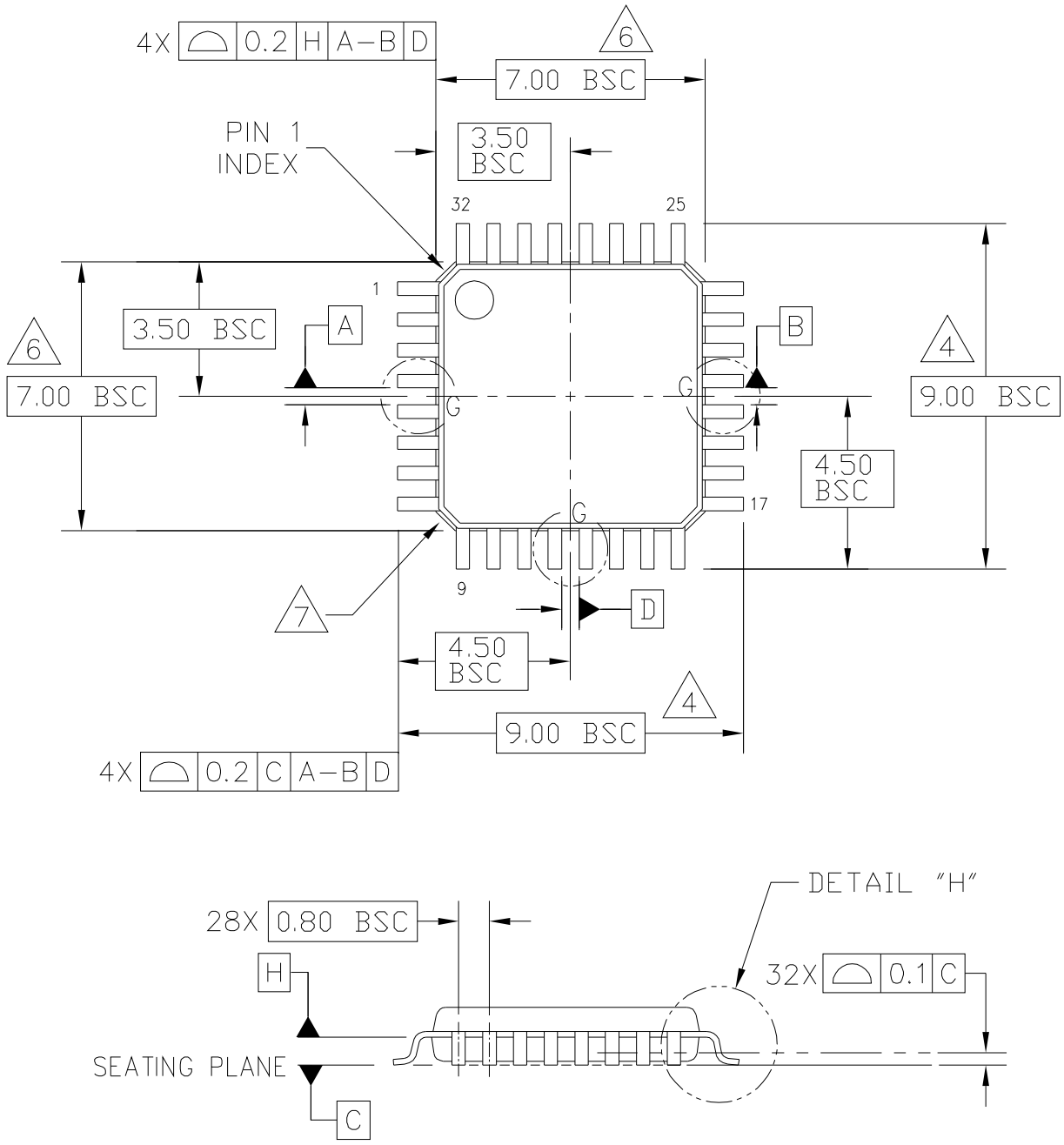
TITLE: 44 LD LQFP, 10 X 10 PKG, 0.8 PITCH, 1.4 THICK	DOCUMENT NO: 98ASS23225W	REV: D
	CASE NUMBER: 824D-02	26 FEB 2007
	STANDARD: JEDEC MS-026 BCB	

Figure 35. 44-pin LQFP Package Drawing (Case 824D, Doc #98ASS23225W), Sheet 3 of 3



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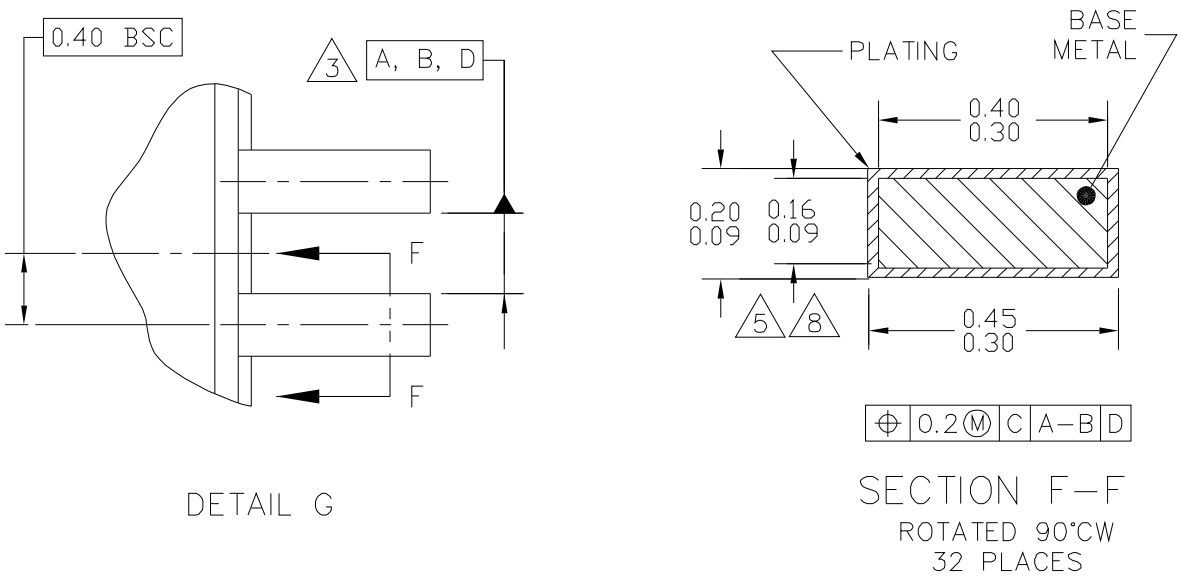
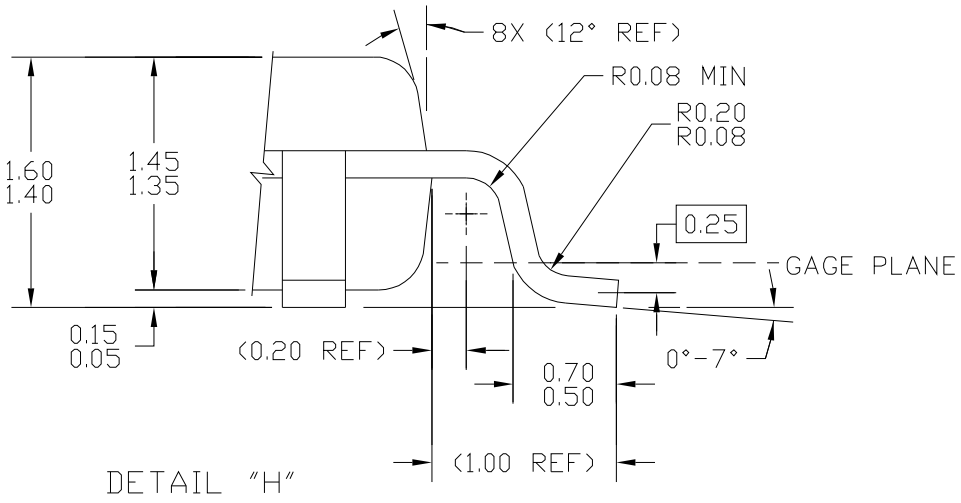
TITLE: LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	DOCUMENT NO: 98ASH70029A	REV: D
	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	

Figure 36. 32-pin LQFP Package Drawing (Case 873A, Doc #98ASH70029A), Sheet 1 of 3





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TITLE: LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	DOCUMENT NO: 98ASH70029A	REV: D
	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	

Figure 37. 32-pin LQFP Package Drawing (Case 873A, Doc #98ASH70029A), Sheet 2 of 3

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5–1994.

3. DATUMS A, B, AND D TO BE DETERMINED AT DATUM PLANE H.

4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE DATUM C.

5. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE MAXIMUM DIMENSION BY MORE THAN 0.08 MM. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION: 0.07 MM.

6. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 MM PER SIDE. DIMENSIONS ARE MAXIMUM PLASTIC BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH.

7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.

8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 MM AND 0.25 MM FROM THE LEAD TIP.

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TITLE: LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)	DOCUMENT NO: 98ASH70029A	REV: D
	CASE NUMBER: 873A-03	19 MAY 2005
	STANDARD: JEDEC MS-026 BBA	

Figure 38. 32-pin LQFP Package Drawing (Case 873A, Doc #98ASH70029A), Sheet 3 of 3